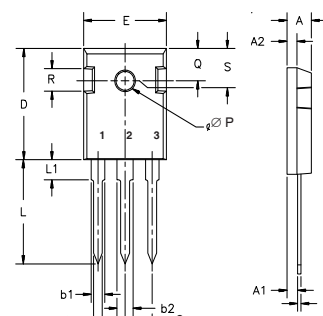


Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 16\text{A}$, $V_{CE} = 10\text{V}$, Note 1	8.5	14	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		1960	pF
C_{oes}			85	pF
C_{res}			24	pF
Q_g	$I_C = 16\text{A}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		72	nC
Q_{ge}			12	nC
Q_{gc}			25	nC
$t_{d(on)}$	Resistive Switching times, $T_J = 25^\circ\text{C}$ $I_C = 16\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 850\text{V}$, $R_G = 22\Omega$		38	ns
t_r			101	ns
$t_{d(off)}$			125	ns
t_f			480	ns
$t_{d(on)}$	Resistive Switching times, $T_J = 125^\circ\text{C}$ $I_C = 16\text{A}$, $V_{GE} = 15\text{V}$ $V_{CE} = 850\text{V}$, $R_G = 22\Omega$		37	ns
t_r			183	ns
$t_{d(off)}$			235	ns
t_f			705	ns
R_{thJC}				0.50 $^\circ\text{C/W}$
R_{thCS}		0.25		$^\circ\text{C/W}$

TO-247 (IXBH) Outline



Terminals: 1 - Gate
2 - Drain
3 - Source
Tab - Drain

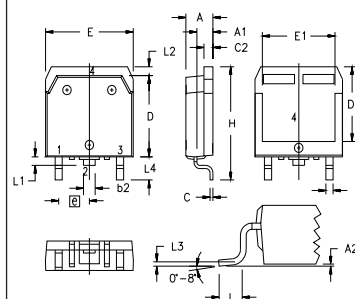
Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Reverse Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$ unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 16\text{A}$, $V_{GE} = 0\text{V}$			2.6 V
t_{rr}	$I_F = 8\text{A}$, $V_{GE} = 0\text{V}$, $-di_F/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}$, $V_{GE} = 0\text{V}$		1.32	μs
I_{RM}			26	A

Note 1: Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-268 (IXBT) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A1	.106	.114	2.70	2.90
A2	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b2	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics
@ 25°C

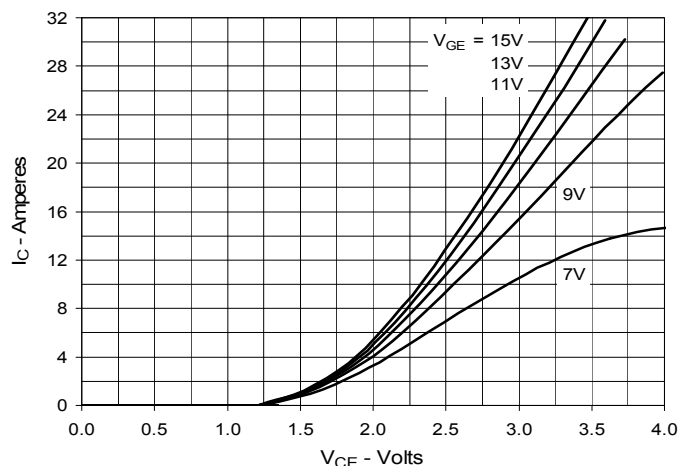


Fig. 2. Extended Output Characteristics
@ 25°C

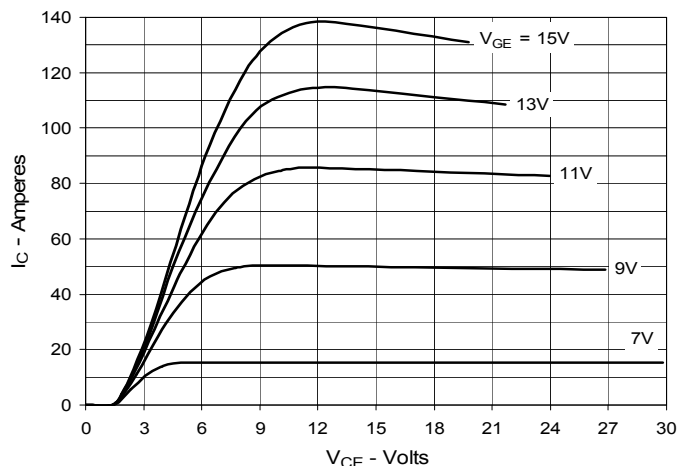


Fig. 3. Output Characteristics
@ 125°C

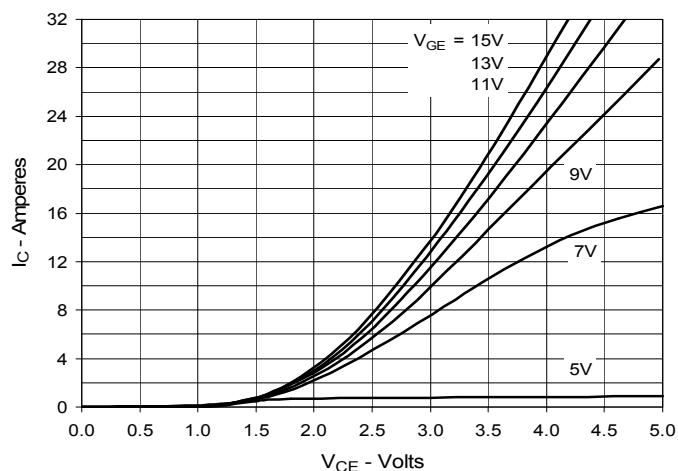


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

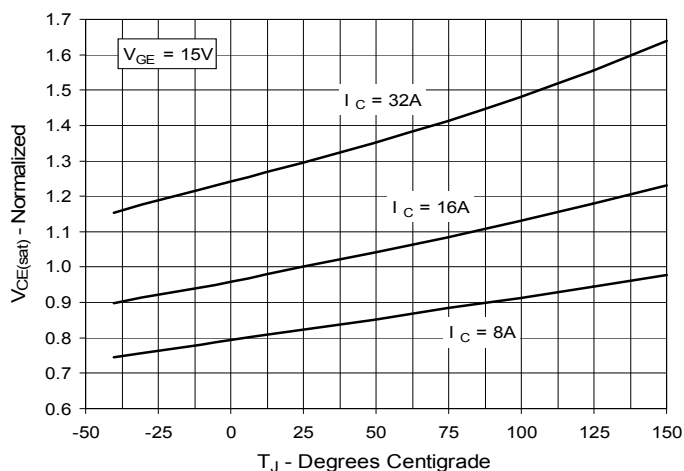


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

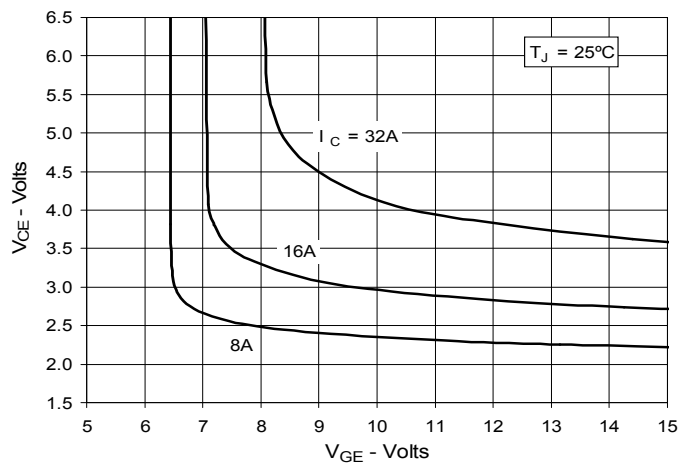


Fig. 6. Input Admittance

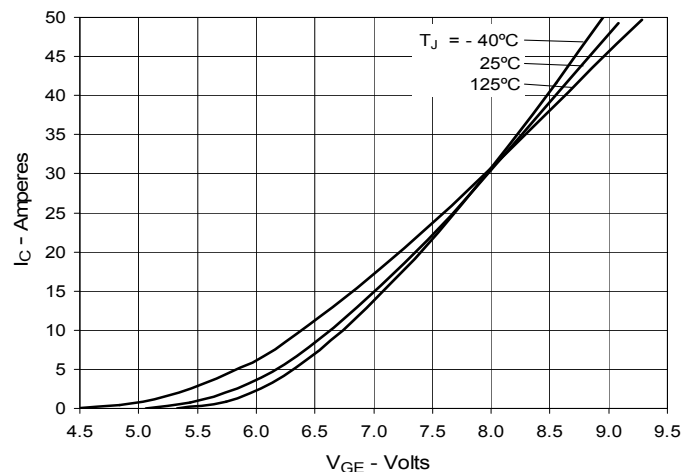


Fig. 7. Transconductance

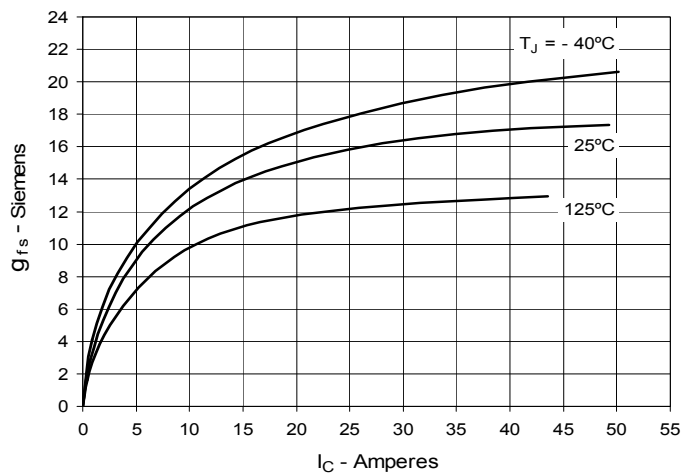


Fig. 8. Forward Voltage Drop of Intrinsic Diode

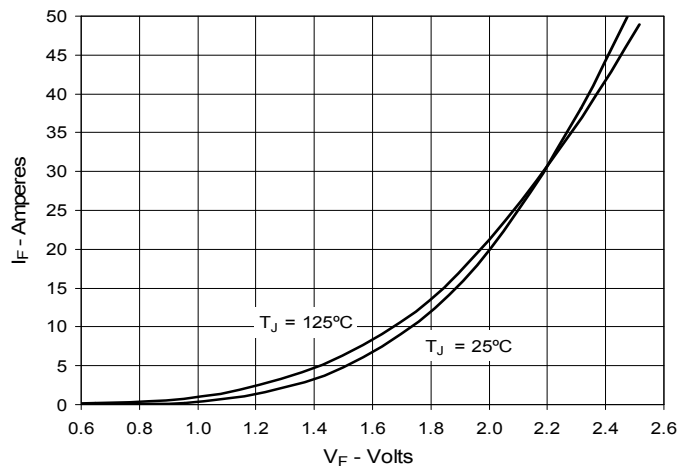


Fig. 9. Gate Charge

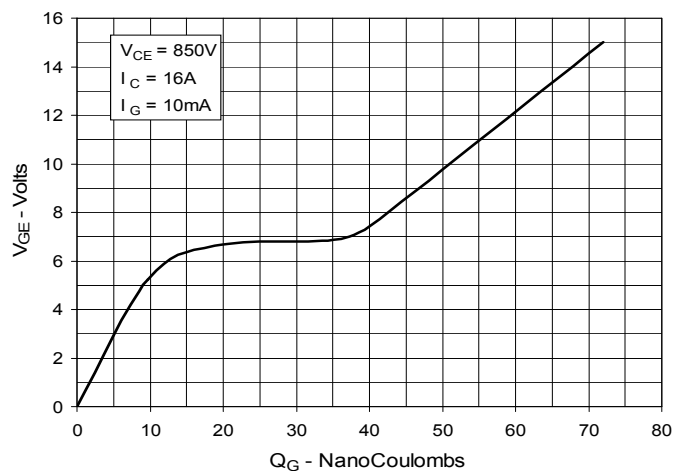


Fig. 10. Capacitance

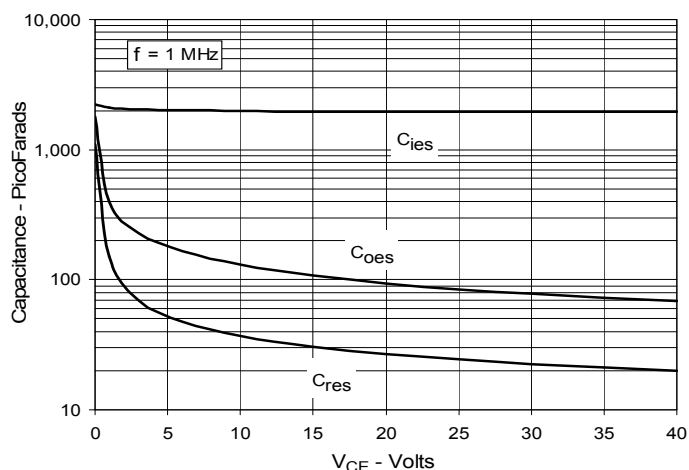


Fig. 11. Reverse-Bias Safe Operating Area

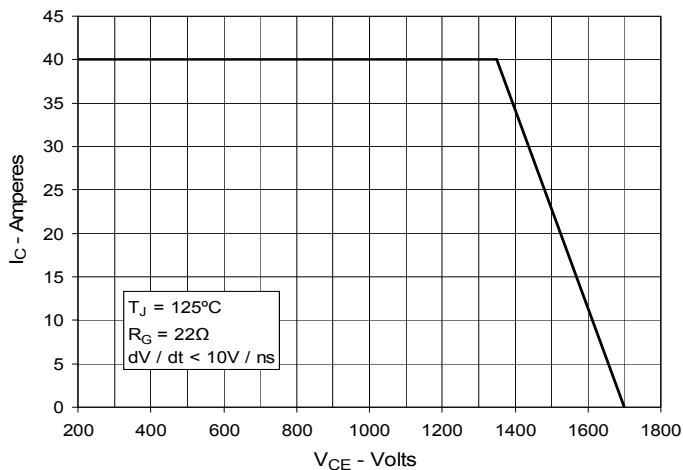
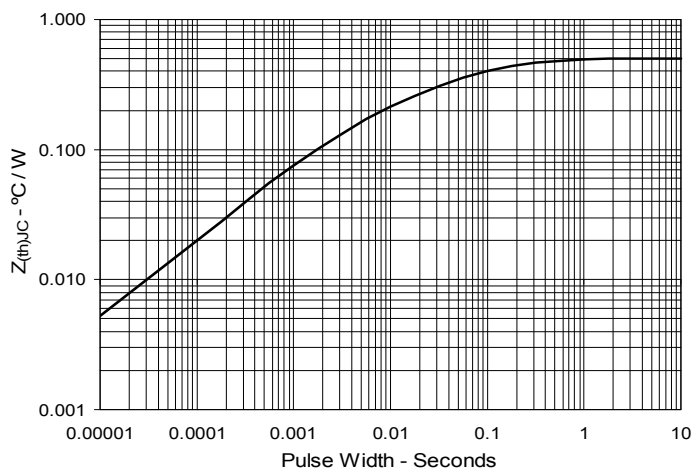
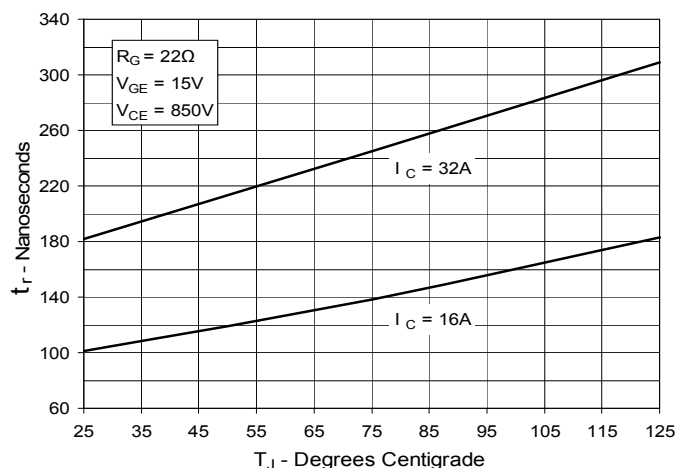


Fig. 12. Maximum Transient Thermal Impedance

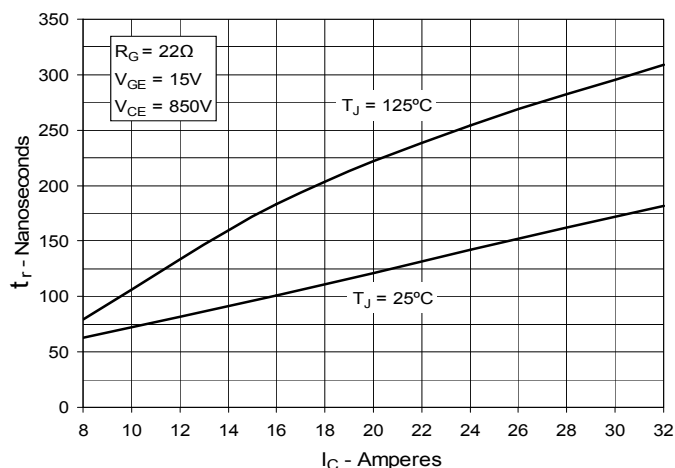


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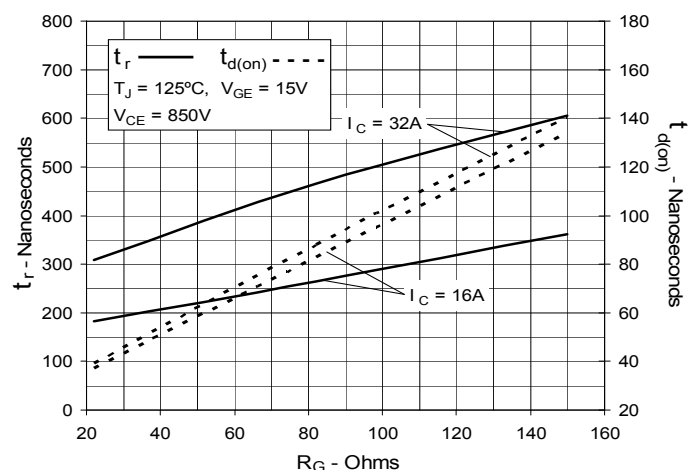
**Fig. 13. Resistive Turn-on
Rise Time vs. Junction Temperature**



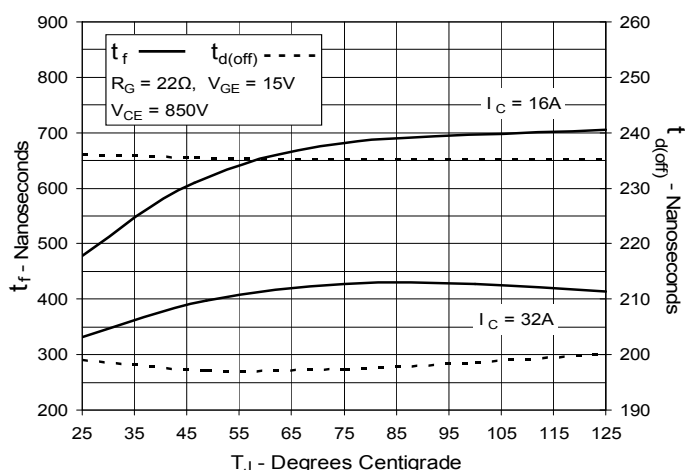
**Fig. 14. Resistive Turn-on
Rise Time vs. Drain Current**



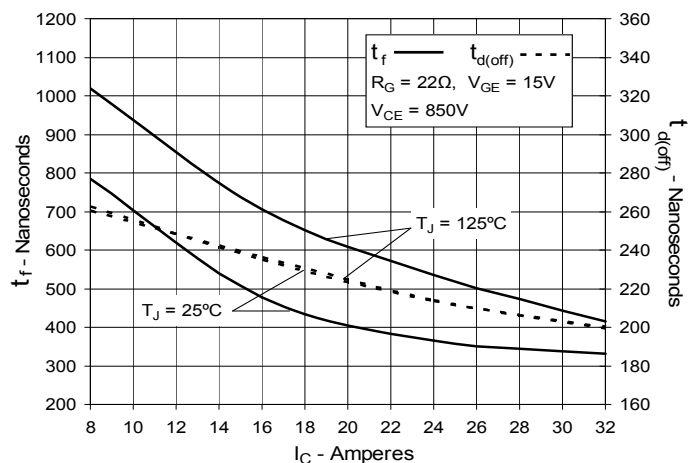
**Fig. 15. Resistive Turn-on
Switching Times vs. Gate Resistance**



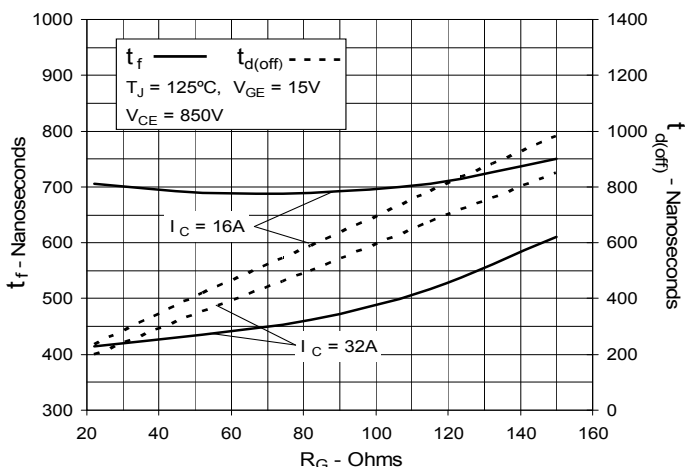
**Fig. 16. Resistive Turn-off
Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off
Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off
Switching Times vs. Gate Resistance**





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